

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	727	349/38	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/07/04 16:17
L2	27	1 and (gate scanning) with oxide adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/07/04 16:17
L3	672	349/39	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/07/04 16:17
L4	10	1 and storage with oxide adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/07/04 16:19
L5	19	1 and capacit\$4 with oxide adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/07/04 16:22
L6	149	1 and thin adj film with (opening contact\$3 adj hole)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/07/04 16:24
L7	100	6 and silicon adj (oxide nitride)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/07/04 16:24
L8	23	6 and top adj gate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/07/04 16:28
L9	73	1 and semiconductor adj energy	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/07/04 16:35
L10	52	3 and semiconductor adj energy	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/07/04 16:35